

## Description

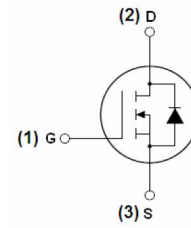
The **vs65N03-T2** uses advanced trench technology and design to provide excellent  $R_{DS(ON)}$  with low gate charge. It can be used in a wide variety of applications.

## General Features

- $V_{DS} = 30V, I_D = 65A$   
 $R_{DS(ON)} < 7.0m\Omega @ V_{GS} = 10V$   
 $R_{DS(ON)} < 9.5m\Omega @ V_{GS} = 5V$
- High density cell design for ultra low  $R_{dson}$
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high  $E_{AS}$
- Excellent package for good heat dissipation

## Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply



**Schematic diagram**



## Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
<b>VS65N03-T2</b>	<b>VS65N03-T2</b>	TO-252-2L	-	-	-

## Absolute Maximum Ratings ( $T_c = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	$V_{DS}$	30	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current-Continuous	$I_D$	65	A
Drain Current-Continuous( $T_c = 100^\circ\text{C}$ )	$I_D(100^\circ\text{C})$	46	A
Pulsed Drain Current	$I_{DM}$	200	A
Maximum Power Dissipation	$P_D$	65	W
Derating factor		0.43	W/ $^\circ\text{C}$
Single pulse avalanche energy <sup>(Note 5)</sup>	$E_{AS}$	150	mJ
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 To 175	$^\circ\text{C}$

## Thermal Characteristic

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	$R_{\theta JC}$	2.3	$^\circ\text{C/W}$
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**Electrical Characteristics (TC=25°C unless otherwise noted)**

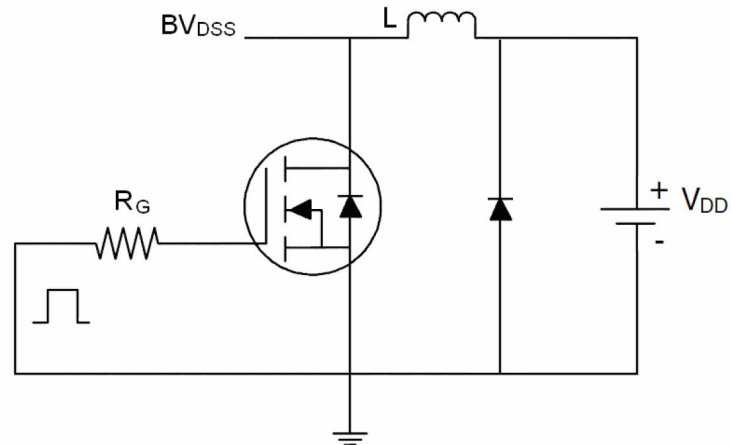
Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	30	-	-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±100	nA
On Characteristics <sup>(Note 3)</sup>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	1	1.5	2.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	5.7	7.0	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =20A	-	7.7	9.5	
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =5V, I <sub>D</sub> =20A	20	-	-	S
Dynamic Characteristics <sup>(Note4)</sup>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, F=1.0MHz	-	1400	-	PF
Output Capacitance	C <sub>oss</sub>		-	205	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	177	-	PF
Switching Characteristics <sup>(Note 4)</sup>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =5V, I <sub>D</sub> =20A V <sub>GS</sub> =10V, R <sub>GEN</sub> =6Ω	-	9	-	nS
Turn-on Rise Time	t <sub>r</sub>		-	8	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	28	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	5	-	nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =20A, V <sub>GS</sub> =10V	-	32.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	4.9	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	6.9	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage <sup>(Note 3)</sup>	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =20A	-	0.85	1.2	V
Diode Forward Current <sup>(Note 2)</sup>	I <sub>S</sub>		-	-	65	A
Reverse Recovery Time	t <sub>rr</sub>	T <sub>J</sub> = 25°C, I <sub>F</sub> = 20A di/dt = 100A/μs <sup>(Note3)</sup>	-	-	27	nS
Reverse Recovery Charge	Q <sub>rr</sub>		-	-	20	nC
Forward Turn-On Time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

**Notes:**

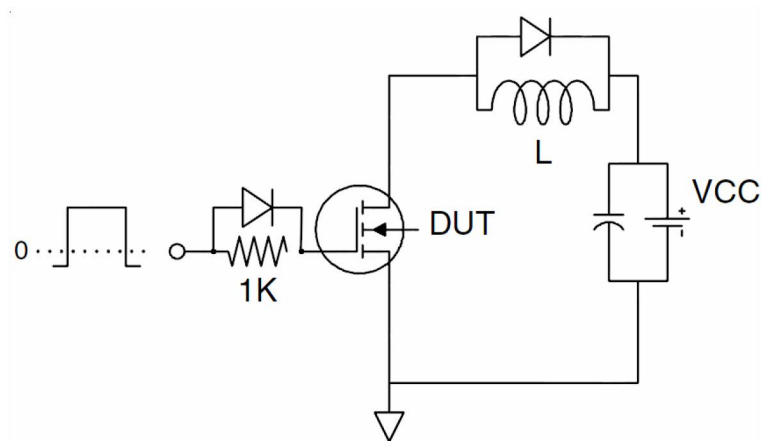
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board,  $t \leq 10$  sec.
3. Pulse Test: Pulse Width  $\leq 300\mu s$ , Duty Cycle  $\leq 2\%$ .
4. Guaranteed by design, not subject to production
5. EAS condition:  $T_J=25^\circ C, V_{DD}=15V, V_G=10V, L=0.5mH, R_g=25\Omega$

## Test Circuit

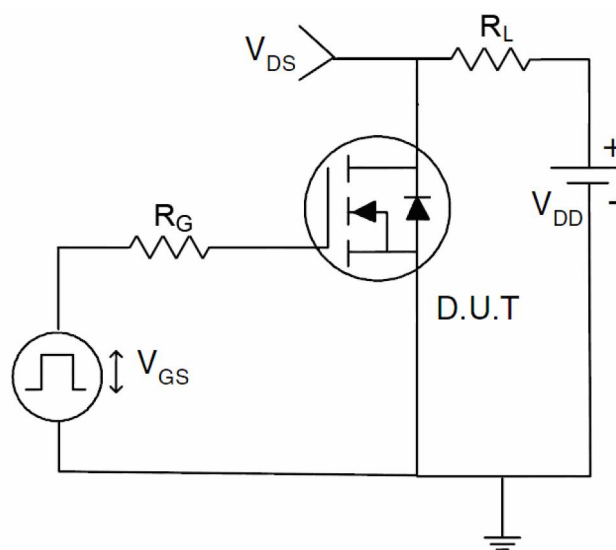
### 1) $E_{AS}$ Test Circuits



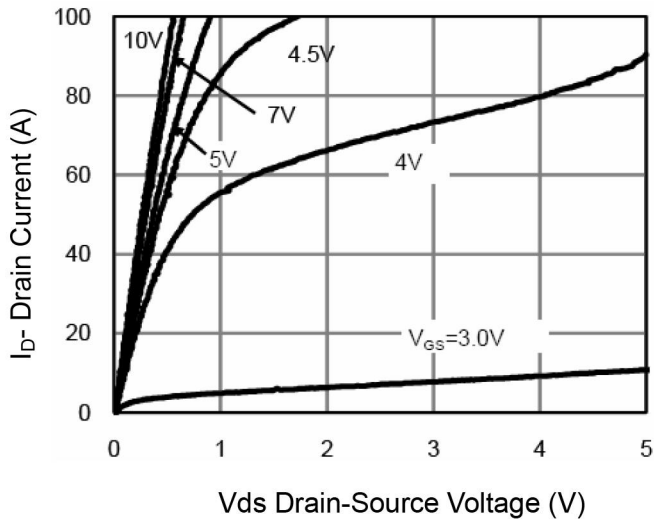
### 2) Gate Charge Test Circuit



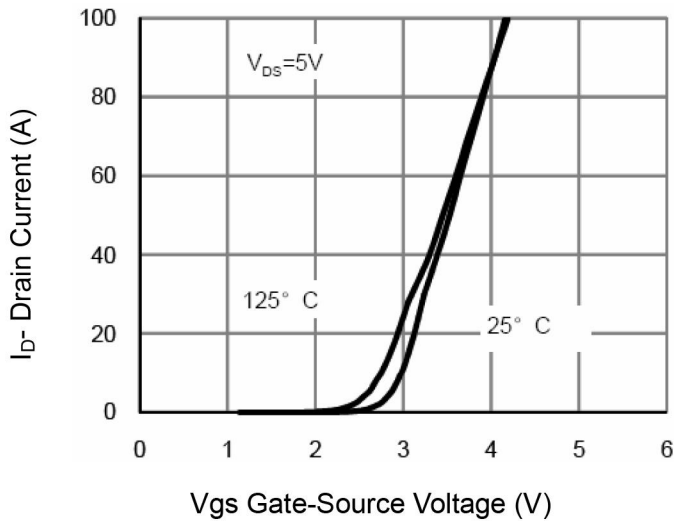
### 3) Switch Time Test Circuit



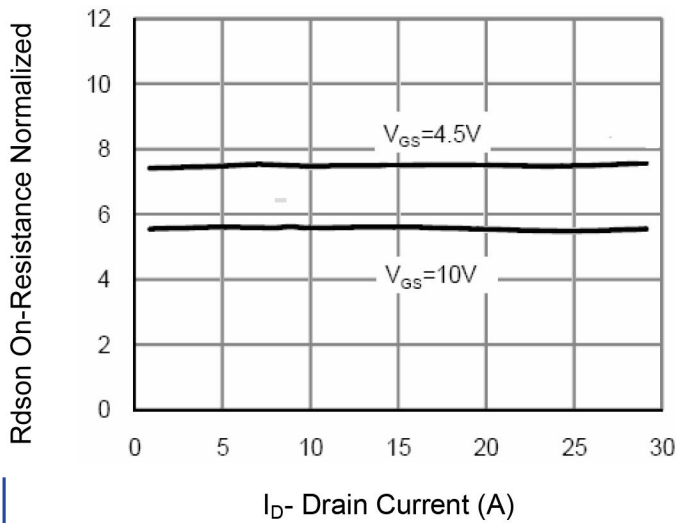
## Typical Electrical and Thermal Characteristics (Curves)



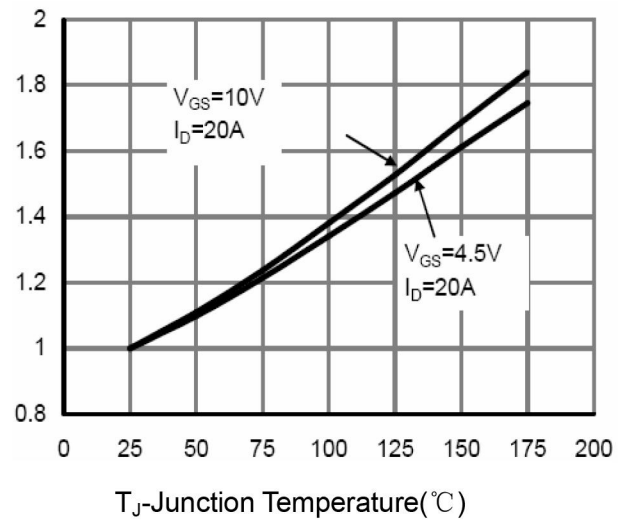
**Figure 1 Output Characteristics**



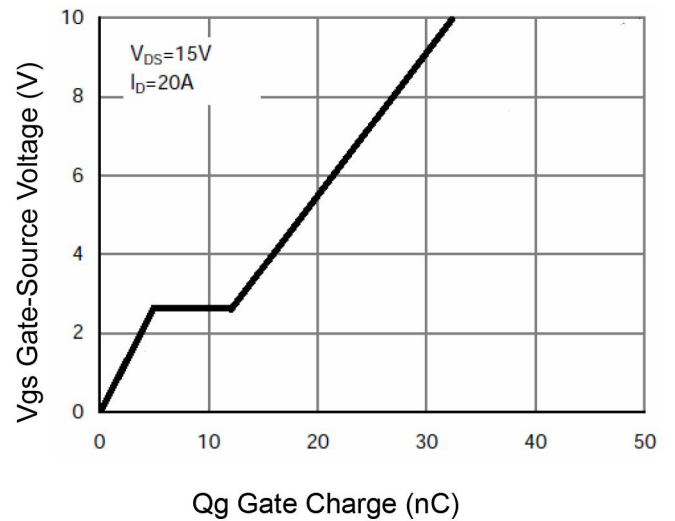
**Figure 2 Transfer Characteristics**



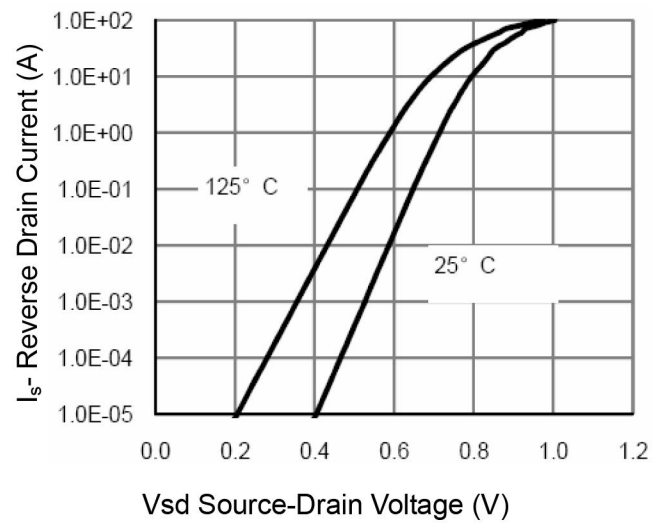
**Figure 3  $R_{DS(on)}$ - Drain Current**



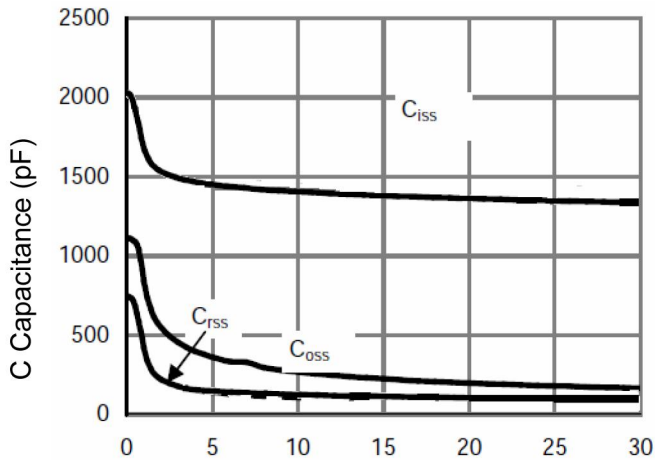
**Figure 4  $R_{DS(on)}$ -Junction Temperature**



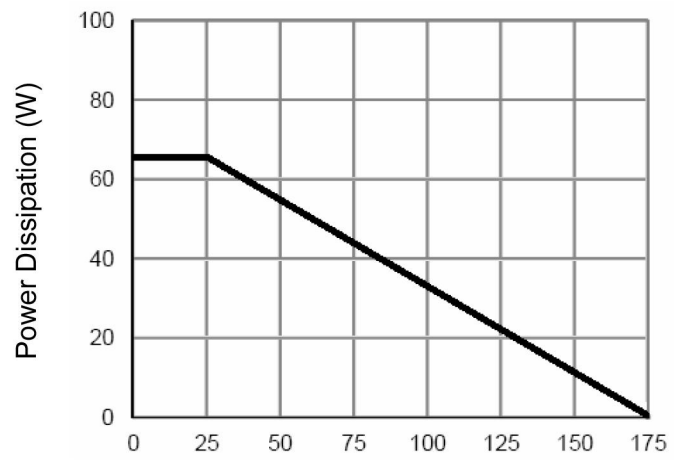
**Figure 5 Gate Charge**



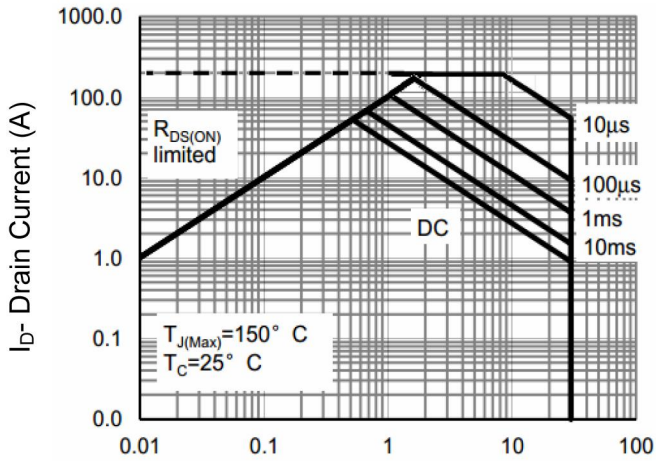
**Figure 6 Source- Drain Diode Forward**



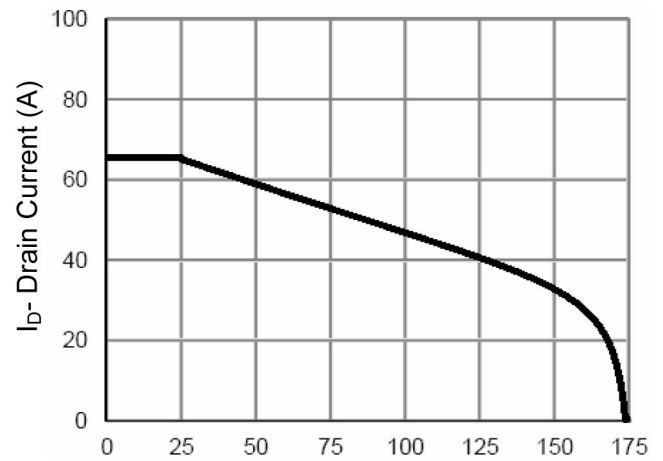
Vds Drain-Source Voltage (V)  
**Figure 7 Capacitance vs Vds**



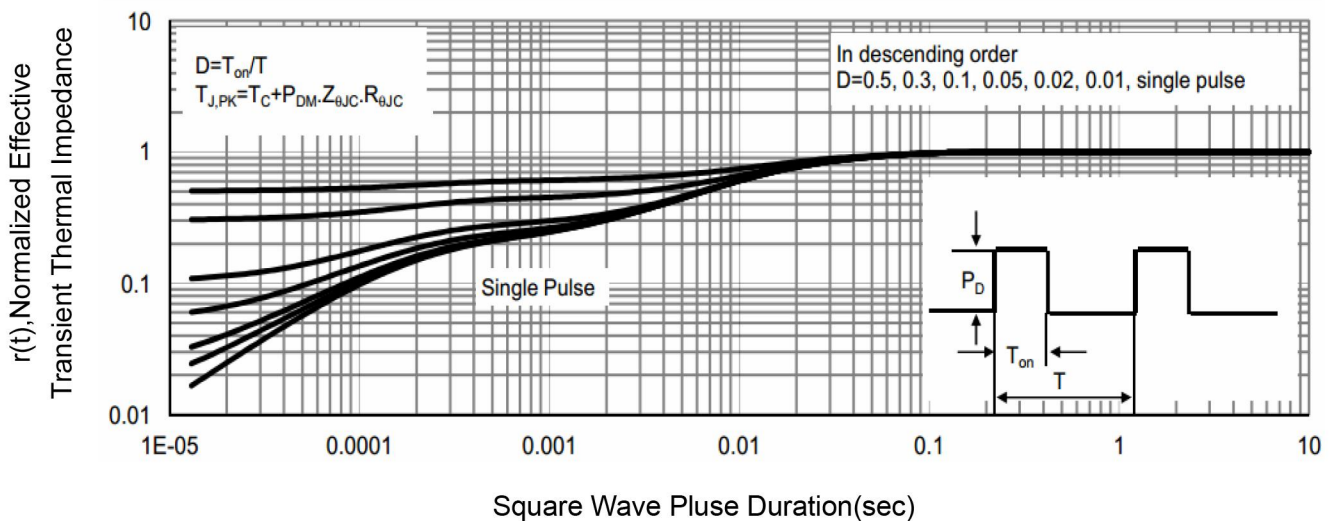
TJ-Junction Temperature(°C)  
**Figure 9 Power De-rating**



Vds Drain-Source Voltage (V)  
**Figure 8 Safe Operation Area**



TJ-Junction Temperature(°C)  
**Figure10 ID Current- Junction Temperature**



**Figure 11 Normalized Maximum Transient Thermal Impedance**